







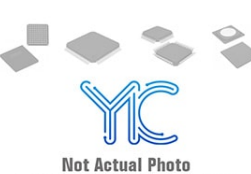
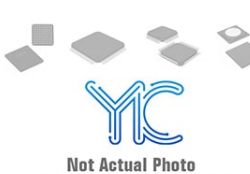
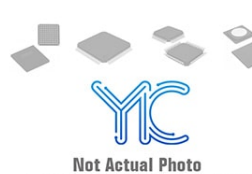
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|  | <h2>SIR158DP-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SIR158DP-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 60A PPAK SO-8</p> <p>Datenblätter:  SIR158DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 36038 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

| | |
|--|---|
| Teilenummer | SIR158DP-T1-GE3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET N-CH 30V 60A PPAK SO-8 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs , |
| Teilstatus | 36038 pcs Stock |
| Hersteller Standard Vorlaufzeit | 27 Weeks |
| detaillierte Beschreibung | N-Channel 30V 60A (Tc) 5.4W (Ta), 83W (Tc) Surface |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | PowerPAK® SO-8 |
| Supplier Device-Gehäuse | PowerPAK® SO-8 |
| Verlustleistung (max) | 5.4W (Ta), 83W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 30V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 60A (Tc) |
| Rds On (Max) @ Id, Vgs | 1.8 mOhm @ 20A, 10V |
| VGS (th) (Max) @ Id | 2.5V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 130nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 4980pF @ 15V |
| Antriebsspannung (Max Rds On, Min Rds On) | 4.5V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Cut Tape (CT) |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |
| Andere Namen | SIR158DP-T1-GE3CT |

SIR158DP-T1-GE3 ist neu im Original, Suche SIR158DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIR158DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIR158DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|---|---|--|---|
|  <p>SIR158DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 60A PPAK SO-8</p> |  <p>SIR158DP-T1-E3 VISHAY SIR158DP-T1-E3 VISHAY</p> |  <p>SIR164ADP-T1-GE3 QQ2850920 SIR164ADP-T1-GE3 QQ2850920</p> |  <p>SIR158DP SI SIR158DP SI</p> |
|  <p>SIR158DP-T1-RE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A POWERPAKSO-8</p> |  <p>SIR164DP SI SIR164DP SI</p> |  <p>SIR158 VISHAY VISHAY QFN</p> |  <p>SIR149DP-T1-E3 VISHAY VISHAY QFN8</p> |

heiße Teile

Mehr

| | | | | |
|--------------------|-------------------|---------------------|--------------------|-------------------|
| ⊕ SIR-312STT32 | ↔ SIR-34ST3F | ⇒ SIR-563ST3F | D SIR-563ST3FM | ↔ SIR-563ST3FN |
| ⊕ SIR-563ST3FP | ⊕ SIR-563ST3FX | D SIR-56SB3F | ⇒ SIR-56ST3F | ↔ SIR-59SSTA47 |
| ⊕ SIR11-21C/TR8 | ⊕ SIR15-21C/TR8 | ⊕ SIR158DP | ↔ SIR158DP-T1-E3 | ↔ SIR158DP-T1-GE3 |
| D SIR164ADP-T1-GE3 | ⊕ SIR164DP | ⊕ SIR164DP-T1-E3 | ⊕ SIR164DP-T1-GE3 | ↔ SIR164DP-T1-GE3 |
| ⇒ SIR166DP | ↔ SIR166DP-T1-E3 | ⊕ SIR166DP-T1-GE3 | ⊕ SIR166DP-T1-GE3 | ↔ SIR168DP |
| ↔ SIR168DP-T1-GE3 | ⇒ SIR168DP-T1-GE3 | D SIR172ADP-T1-GE3 | ⊕ SIR172ADP-T1-GE3 | ⊕ SIR172DP |
| ⊕ SIR172DP-T1-E3 | D SIR172DP-T1-GE3 | ⇒ SIR172DP-T1-GE3 | ↔ SIR330DP-T1-GE3 | ↔ SIR330DP-T1-GE3 |
| ⊕ SIR402DP-T1-GE3 | ⊕ SIR402DP-T1-GE3 | ↔ SIR403EDP-T1-GE3 | ⇒ SIR403EDP-T1-GE3 | ↔ SIR404DP |
| ⊕ SIR404DP-T1-E3 | ⊕ SIR404DP-T1-GE3 | ⊕ SIR404DP-T1-GE3 | D SIR406DP | ↔ SIR406DP-T1-E3 |
| ↔ SIR406DP-T1-GE3 | ⊕ SIR406DP-T1-GE3 | ⊕ SIR406DP-T1-GE3-S | ⊕ SIR408DP-T1-GE3 | ↔ SIR408DP-T1-GE3 |

Contact us: Info@Y-IC.com

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